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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10010484	FILING DATE 11/20/2001	CLASS 257	SUBCLASS 330	GAU 2826	EXAMINER GARIBOLDI TAN
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TAN TRAN

**CONTINUING DATA VERIFIED: NO /1

** FOREIGN APPLICATIONS VERIFIED: NO /1

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed 115 USC 119 conditions met		<input type="checkbox"/> yes <input checked="" type="checkbox"/> no <input type="checkbox"/> yes <input checked="" type="checkbox"/> no	ATTORNEY DOCKET NO
Verified and Acknowledged Examiners's initials		T	GS 150
TITLE : Trench MOSFET device with polycrystalline silicon source contact structure U.S. DEPT. OF COMM/PAT & TM-PTO-436L(Rev. 12-94)			

NOTICE OF ALLOWANCE MAILED		TAN TRAN Assistant Examiner 07/03	CLAIMS ALLOWED	
			Total Claims 16	Print Claim for O.G. 1
ISSUE FEE		DRAWING		
Amount Due	Date Paid	Sheets Drwg. 5	Figs.Drwg. 10	Print Fig. 3A
		Primary Examiner		
		PREPARED FOR ISSUE		
		Application Examiner		
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